ELECTRONICS, INC.
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NTE2354

Silicon NPN Transistor

High Voltage Horizontal Output for High Definition CRT

Applications:

- High–definition color display horizontal deflection output

Features:

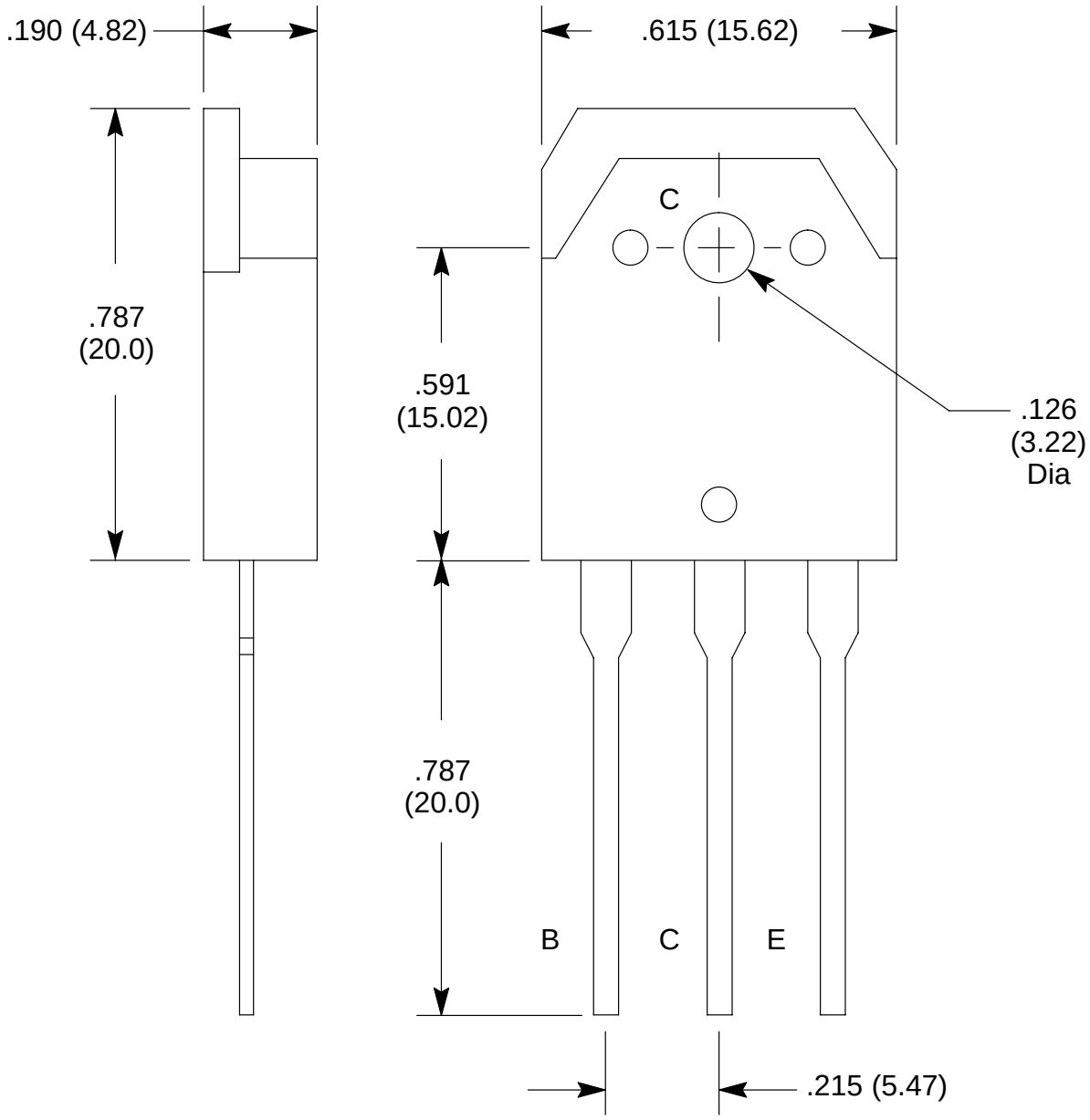
- Fast speed: t_f = 100ns Typ
- High breakdown voltage: V_{CBO} = 1500V
- High reliability

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Collector–to–Base Voltage, V_{CBO} 1500V
Collector–to–Emitter Voltage, V_{CEO} 800V
Emitter–to–Base Voltage, V_{EBO} 6V
Collector Current, I_C 10A
Peak Collector Current, i_{cp} 25A
Collector Dissipation (T_C = +25°C), P_C 150W
Junction Temperature, T_J . . . . . +150°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CES}	V_{CE} = 1500V, R_{BE} = 0	–	–	1.0	mA
Collector Sustain Voltage	$V_{CEO(sus)}$	I_C = 100mA, I_B = 0	800	–	–	V
Emitter Cutoff Current	I_{EBO}	V_{EB} = 4V, I_C = 0	–	–	1.0	mA
Saturation Voltage Collector–to–Emitter	$V_{CE(sat)}$	I_C = 8A, I_B = 2.0A	–	–	5.0	V
Saturation Voltage Base–to–Emitter	$V_{BE(sat)}$	I_C = 8A, I_B = 2.0A	–	–	1.5	V
DC Current Gain	h_{FE}	V_{CE} = 5V, I_C = 1.0A	8	–	–	–
Storage Time	t_{stg}	I_C = 6A, I_{B1} = 1.2A, I_{B2} = –2.4A	–	–	3.0	µs
Fall Time	t_f	I_C = 6A, I_{B1} = 1.2A, I_{B2} = –2.4A	–	0.1	0.2	µs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